

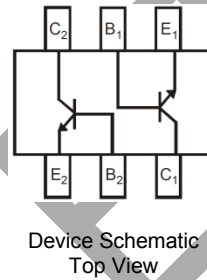
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**Features**

- $BV_{CE0} > 25V$
- $I_C = 200mA$
- Complementary PNP Type Available (MMDT4126)
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

**Mechanical Data**

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Finish; Solderable per MIL-STD-202, Method 208③
- Weight: 0.006 grams (Approximate)

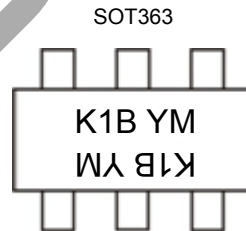


**Ordering Information** (Note 4)

Part Number	Status	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMDT4124-7-F	Active	AEC-Q101	K1B	7	8	3,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

**Marking Information**



K1B = Product Type Marking Code  
 YM = Date Code Marking  
 Y or  $\bar{Y}$  = Year (ex: D = 2016)  
 M or  $\bar{M}$  = Month (ex: 9 = September)

**Date Code Key**

Year	2016	2017	2018	2019	2020	2021	2022	2023
Code	D	E	F	G	H	I	J	K

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	30	V
Collector-Emitter Voltage	V <sub>CEO</sub>	25	V
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	V
Collector Current	I <sub>C</sub>	200	mA

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	625	°C/W
Operating and Storage and Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**ESD Ratings** (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
- For the device mounted on minimum recommended pad layout FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

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**Thermal Characteristic and Derating Information**

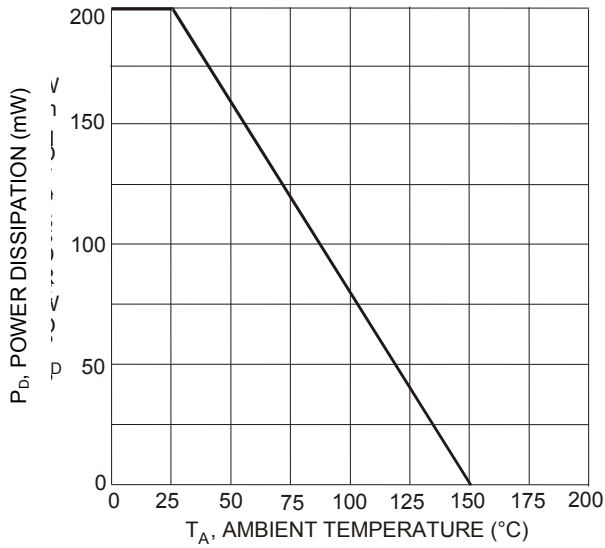


Figure 1. Power Dissipation vs. Ambient Temperature (Total Device)

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**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>					
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	30	—	V	I <sub>C</sub> = 10μA, I <sub>E</sub> = 0
Collector-Emitter Breakdown Voltage (Note 7)	BV <sub>CEO</sub>	25	—	V	I <sub>C</sub> = 1.0mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	5.0	—	V	I <sub>E</sub> = 10μA, I <sub>C</sub> = 0
Collector-Base Cut-Off Current	I <sub>CBO</sub>	—	50	nA	V <sub>CB</sub> = 20V
Emitter-Base Cut-Off Current	I <sub>EBO</sub>	—	50	nA	V <sub>EB</sub> = 3V
<b>ON CHARACTERISTICS (Note 7)</b>					
DC Current Gain	h <sub>FE</sub>	120 60	360 —	—	I <sub>C</sub> = 2.0mA, V <sub>CE</sub> = 1.0V I <sub>C</sub> = 50mA, V <sub>CE</sub> = 1.0V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	—	0.30	V	I <sub>C</sub> = 50mA, I <sub>B</sub> = 5.0mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	—	0.95	V	I <sub>C</sub> = 50mA, I <sub>B</sub> = 5.0mA
<b>SMALL SIGNAL CHARACTERISTICS</b>					
Output Capacitance	C <sub>obo</sub>	—	4.0	pF	V <sub>CB</sub> = 5.0V, f = 1.0MHz, I <sub>E</sub> = 0
Input Capacitance	C <sub>ibo</sub>	—	8.0	pF	V <sub>EB</sub> = 0.5V, f = 1.0MHz, I <sub>C</sub> = 0
Small Signal Current Gain	h <sub>fe</sub>	120	480	—	V <sub>CE</sub> = 1.0V, I <sub>C</sub> = 2.0mA, f = 1.0kHz
Current Gain-Bandwidth Product	f <sub>T</sub>	300	—	MHz	V <sub>CE</sub> = 20V, I <sub>C</sub> = 10mA, f = 100MHz
Noise Figure	NF	—	5.0	dB	V <sub>CE</sub> = 5.0V, I <sub>C</sub> = 100μA, R <sub>S</sub> = 1.0kΩ, f = 1.0kHz

Note: 7. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

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**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

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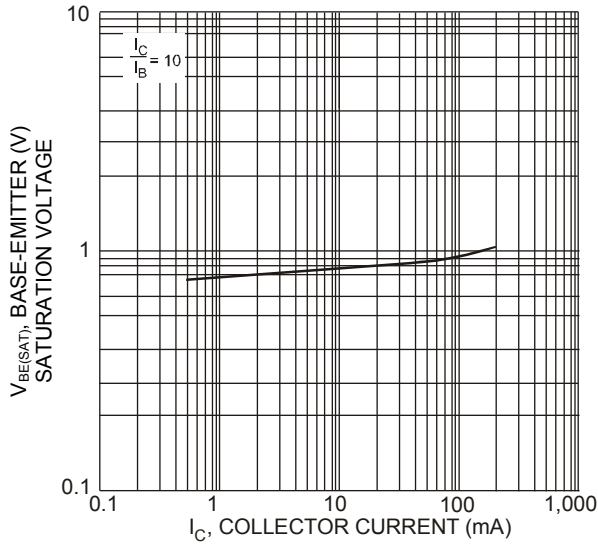


Figure 2. Typical Base-Emitter Saturation Voltage vs. Collector Current

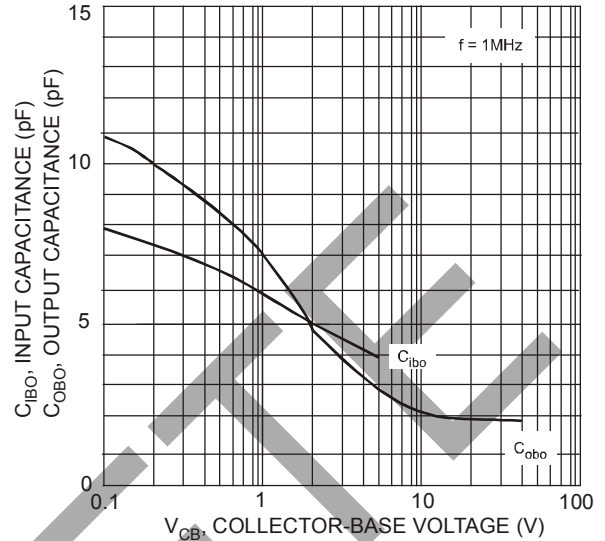


Figure 3. Input and Output Capacitance vs. Collector-Base Voltage

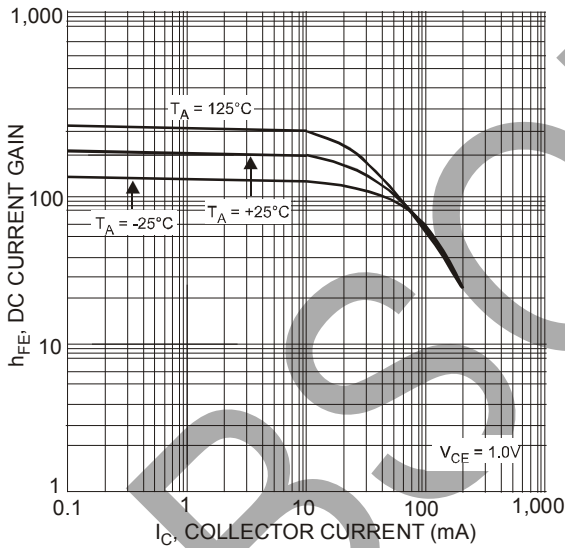


Figure 4. Typical DC Current Gain vs. Collector Current

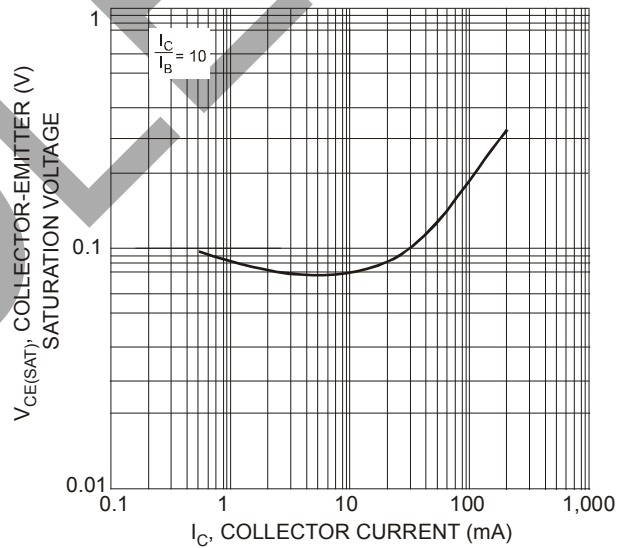
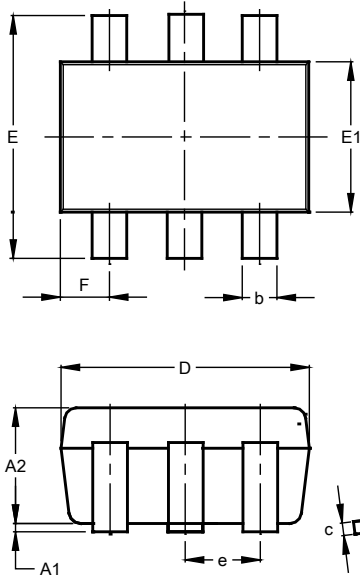


Figure 5. Typical Collector-Emitter Saturation Voltage vs. Collector Current

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT363**

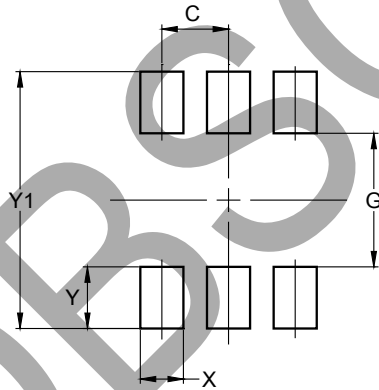


SOT363			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	1.00
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT363**



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

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